EAST - [10759809 trench gate between fox.wsp:1]

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(7) ("5451538" | "5467305" | "5485441" | "5587849" | "5595927" | "5751038"
(7) ("5451538" | "5467305" | "5485441" | "5587849" | "5595927" | "5751038"
(4) 6066874.URPN.
(2535) trench$3 near2 channel
(540689) (FOX field adj oxide STI (isolati$3) LOCOS)
(8692029) (adjacent abut$4 juxtapos$3 proxim$5 adjoin$4 neighboring) two second
(26437) ((adjacent abut$4 juxtapos$3 proxim$5 adjoin$4 neighboring) two second an
(5353) trench$3 near6 channel
(1406915) channel
(1092) channel near9 (((adjacent abut$4 juxtapos$3 proxim$5 adjoin$4 neighboring) t
(40) (trench$3 near2 channel) and (channel near9 (((adjacent abut$4 juxtapos$3 proxi
(18145) channel adj width
(129834) v adj shaped
(46106) ((float$4 adj (gate electrode plate trap$4) FG))
(6782) trench$3 near12 channel
(108) (channel near9 (((adjacent abut$4 juxtapos$3 proxim$5 adjoin$4 neighboring) t
(1524326) memory
(1542045) (((float$4 adj (gate electrode plate trap$4) FG))) memory
(45) ((channel near9 (((adjacent abut$4 juxtapos$3 proxim$5 adjoin$4 neighboring) tv
(2) "20040070050"
(1) 09/953222
(420) (257/317).CCLS.
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((channel near9 (((adjacent abut$4 juxtapos$3 proxim$5 adjoin$4 neighboring) two second another
) near2 ((FOX field adj oxide STI (isolati$3) LOCOS)
))) and (trench$3 near12 channel)) and ((((float$4 adj (gate electrode plate trap$4) FG))) memory)

Sept 2004

	U	↑	Inventor	Document I	Issue	P	Title	Current	Current XR	Retrieval	S	C	P	R	S	B	D	Image Doc.	P
1			Tseng, Kuo-S	US 2003005	20030	8	Method for forming shallow trench isolation	438/257	257/E21.54									US 200300	
2			Trivedi, Jigis	US 6583060	20030	1	Dual depth trench isolation	438/700	257/E21.23									US 658306	
3			Watt, Jeffrey	US 2004004	20040	1	Buried-channel transistor with reduced leaka	438/291	438/298									US 200400	
4			Trivedi, Jigis	US 2003020	20031	1	Dual depth trench isolation	438/200	257/E21.23									US 200302	
5			Lai, Tommy	US 2003020	20031	1	METHOD OF ANGLE IMPLANT TO IMPROVE	438/199	257/E21.54									US 200302	
6			Kawamura, T	US 2003017	20030	1	Trench-gate semiconductor device and its m	438/270	257/397;									US 200301	
7			Kumagai, Yuk	US 2003013	20030	2	Semiconductor device and manufacturing me	257/301	257/303;									US 200301	
8			Ohta, Hiroyuk	US 2003012	20030	2	Semiconductor device	257/390	257/E21.61									US 200301	
9			Weis, Rolf	US 2003008	20030	1	Vertical transistor and transistor fabrication	257/135	257/302;									US 200300	
10			Klersy, Patric	US 2003007	20030	2	Programmable resistance memory element a	257/536	257/E27.00									US 200300	

Ready

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